Six-Element SMD Photodiode Array

OPR2101



Features:

- Six-PIN photodiode array
- High-temperature chip carrier
- Closely matched responsivity between elements
- Easily mountable in any configuration
- Suitable for harsh industrial operating conditions



Description:

Each **OPR2101** device is a six-element photodiode that is designed to meet the needs of motor encoder applications. Designed specifically for *industrial* encoder applications, the miniature-sized **OPR2101** features a high temperature SMD chip carrier, a temperature range and a low leakage current that can withstand extreme operating conditions.

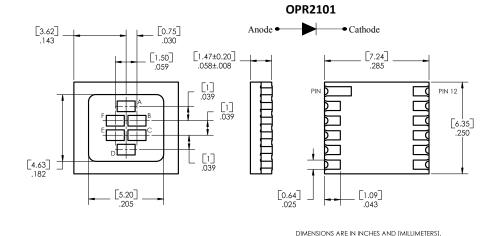
The device has an opaque chip carrier that encloses six individual chips, which are mounted on isolated cathode contacts to allow external connection in any desired configuration. The opaque polyimide package shields the photodiodes from stray light and can withstand multiple exposures to the most demanding soldering conditions, while the gold-plated wraparound solder pads provide exceptional storage and wetting characteristics.

See Application Bulletin 237 for handling instructions.

Applications:

- Motor encoder applications
- Industrial encoder applications

Ordering Information									
Part Number	Sensor	# of Elements	Responsivity (mA/mW) Min	Reverse Voltage Breakdown	Active Area mm ² (each)	Packaging			
OPR2101	Miniature Photodiode Array	6	0.45	50	0.84	Tube			



Pin#	Description		
1	Cathode A		
2	Cathode B		
3	Anode B		
4	Anode C		
5	Cathode C		
6	Cathode D		
7	Anode D		
8	Cathode E		
9	Anode E		
10	Anode F		
11	Cathode F		
12	Anode A		







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Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)		
Storage and Operating Temperature	-55° C to +125° C	
Reverse Voltage	25 V	
Solder reflow time within 5°C of peak temperature is 20 to 40 seconds ⁽¹⁾	250° C	

Electrical	Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS			
R	Responsivity	0.45	-	-	A/W	$E_e = 10 \mu W$, $\lambda = 890 nm$, $V = 0 V$			
V_{BR}	Reverse Breakdown Voltage	50	-	-	V	I _R = 10 μA			
I _D	Reverse Dark Current	-	- 5	5 -	nA μA	V _R = 10 V, E _e = 0 V _R = 10 V, E _e = 0, T _A = 125° C			
B _W	Bandwidth	-	-	55	kHz	T _A ≤ 125ºC			
C _T	Capacitance	-	10	-	pF	V _R = 10 V			
Lx W	Active Area (per diode)	-	0.84	-	mm ²	1.23 mm x .72 mm			

Notes:

1. Solder time less than 5 seconds at temperature extreme.

